



20V LOW $V_{CE(SAT)}$ PNP SURFACE MOUNTED TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Complementary NPN Type Available (ZXTN26020DMF)
- Low Collector-Emitter Saturation Voltage, V_{CE(SAT)}
- High Current Gain (hFE) at High IC
- Surface Mount Package Suited for Automated Assembly
- Ultra-Small Surface Mount Package
- Qualified to AEC-Q101 Standards for High Reliability
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- ESD rating: 400V-MM, 8KV-HBM

Mechanical Data

- Case: DFN1411-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.003 grams (approximate)

Applications

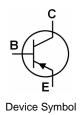
- MOSFET and IGBT gate driving
- DC-DC conversion
- Interface between low voltage IC and Load
- Load disconnect switch



Top view



Bottom view





Pin-Out Top view

Ordering Information

Product	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP26020DMFTA	7	8	3000

Notes: 1. No purposefully added lead. Halogen and Antimony Free.

2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com

Marking Information



Z2= Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009) M = Month (ex: 9 = September)

Date Code Key

Year	2009		2010	2011		2012	2013		2014	2015		2016
Code	W		Х	Y		Z	A		В	С		D
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D





Maximum Ratings

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-20	V
Collector-Emitter Voltage	V _{CEO}	-20	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	lc	-1.25	А
Peak Pulse Current	I _{CM}	-4	A
Base Current(DC)	IB	-0.3	А
Peak Base Current	I _{BM}	-0.6	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	1	W
Power Dissipation (Note 4)	PD	380	mW
Thermal Resistance, Junction to Ambient (Note 3) @ $T_A = 25^{\circ}C$	R _{θJA}	125	°C/W
Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^{\circ}C$	$R_{\theta JA}$	330	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Notes:

Device mounted on FR-4 PCB with 1inch square pads.
Device mounted on FR-4 PCB with minimum recommended pad layout



Electrical Characteristics (at T_A = 25°C unless otherwise specified)

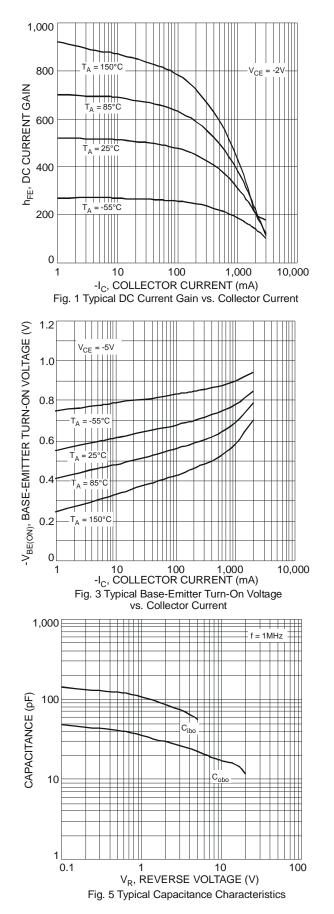
			_			
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-20	—		V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0 A$
Collector-Emitter Breakdown Voltage (Note 5)	V _{(BR)CEO}	-20	—	—	V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0 {\rm A}$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-7	—		V	$I_E = -100 \mu A, I_C = 0A$
Collector Cutoff Current	lcbo			-100	nA	$V_{CB} = -20V, I_E = 0A$
				-0.5	μΑ	$V_{CB} = -20V, I_E = 0A, T_A = 125^{\circ}C$
Emitter Cutoff Current	Ices		—	-100	nA	$V_{CE} = -20V, V_{BE} = 0V$
Base Cutoff Current	lebo	—	_	-50	nA	$V_{BE} = -6V, I_{C} = 0A$
		300	_	_		$V_{CE} = -2V, I_{C} = -100 \text{mA}$
DC Current Gain (Note 5)	h	235	_			$V_{CE} = -2V, I_{C} = -0.5A$
DC Current Gain (Note 5)	h _{FE}	175	—	—		$V_{CE} = -2V, I_{C} = -1A$
		140	—			$V_{CE} = -2V, I_{C} = -1.5A$
	V _{CE(SAT)}	—	—	-80	mV	$I_{\rm C} = -100 {\rm mA}, I_{\rm B} = -1 {\rm mA}$
Collector-Emitter Saturation Voltage (Note 5)		—	—	-100	mV	$I_{\rm C} = -500$ mA, $I_{\rm B} = -50$ mA
g-(····· -)	· CE(GAT)	—	—	-155	mV	$I_{\rm C} = -1A, I_{\rm B} = -50 {\rm mA}$
		—		-235	mV	$I_{\rm C}$ = -1.25A, $I_{\rm B}$ = -62.5mA
Equivalent On-Resistance	R _{CE(SAT)}	_	125		mΩ	I _C = -1A, I _B = -50mA
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_	_	-1.1	V	$V_{CE} = -5V, I_{C} = -1A$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	-1.15	V	I _C = -1A, I _B = -50mA
Output Capacitance (Note 5)	C _{obo}		_	20	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	fT	200	_	_	MHz	V _{CE} = -10V, I _C = -50mA, f = 100MHz
Turn-On Time	t _{on}		60		ns	
Delay Time	t _d		20		ns	7
Rise Time	tr	—	40		ns	$V_{CC} = -10V, I_{C} = -1A$
Turn-Off Time	toff	—	167		ns	$I_{B2} = -I_{B1} = -50 \text{mA}$
Storage Time	ts	—	140	_	ns	7
Fall Time	tf	_	27	_	ns	7

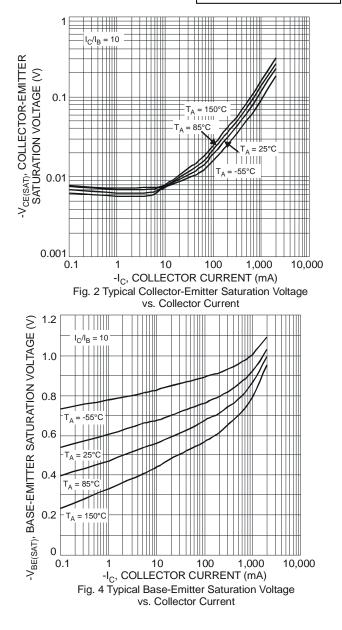
Notes: 5. Short duration pulse test used to minimize self-heating effect.





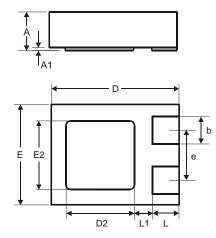






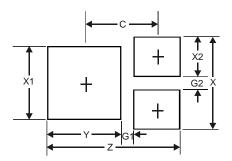


Package Outline Dimensions



DFN1411-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.02		
b	0.25	0.35	0.30		
D	1.35	1.475	1.40		
D2	0.65	0.85	0.75		
Е	1.05	1.18	1.10		
E2	0.65	0.85	0.75		
е	_	_	0.55		
L	0.225	0.325	0.275		
L1	_		0.20		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.38
G1	0.15
G2	0.15
Х	0.95
X1	0.75
X2	0.40
Y	0.75
С	0.76



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